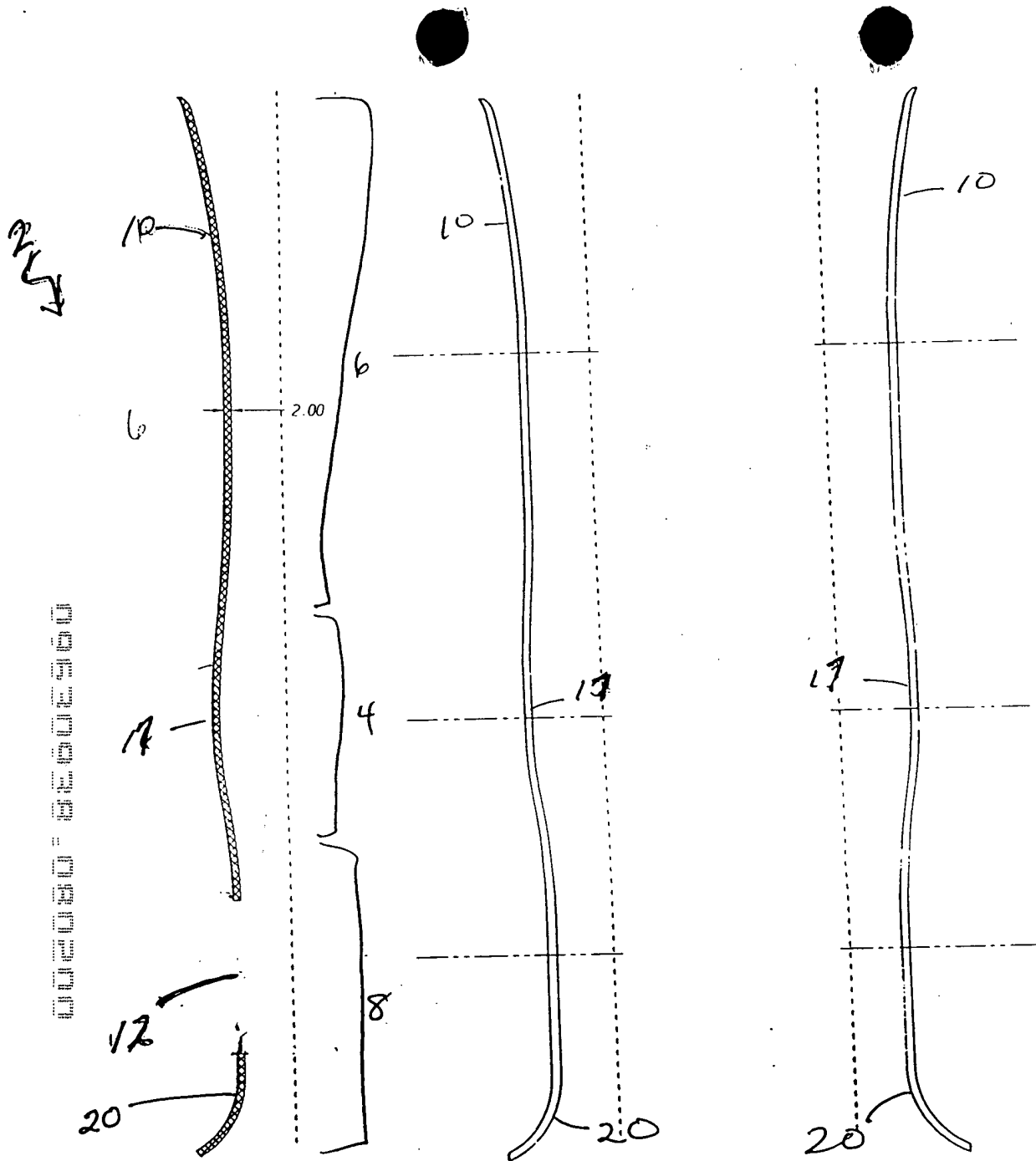


Fig 1A

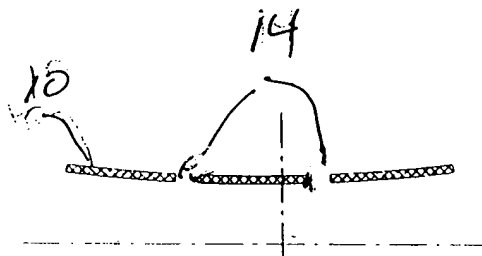


Section 1B-1B

Fig. 1B

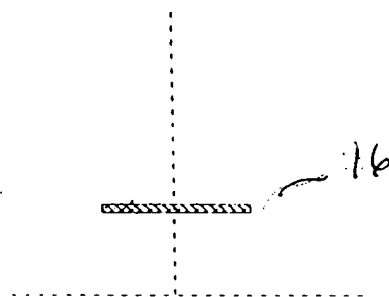
Fig. 1C

Fig. 1D



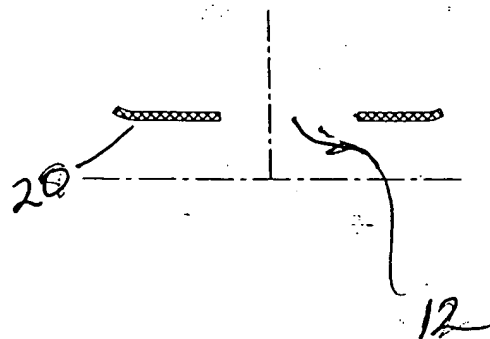
section $1\bar{E}-1\bar{E}$

FIG. 1E



Section 1F-1F

FIG. 1F



Section 1G-1G

FIG. 16

Fig 2 A

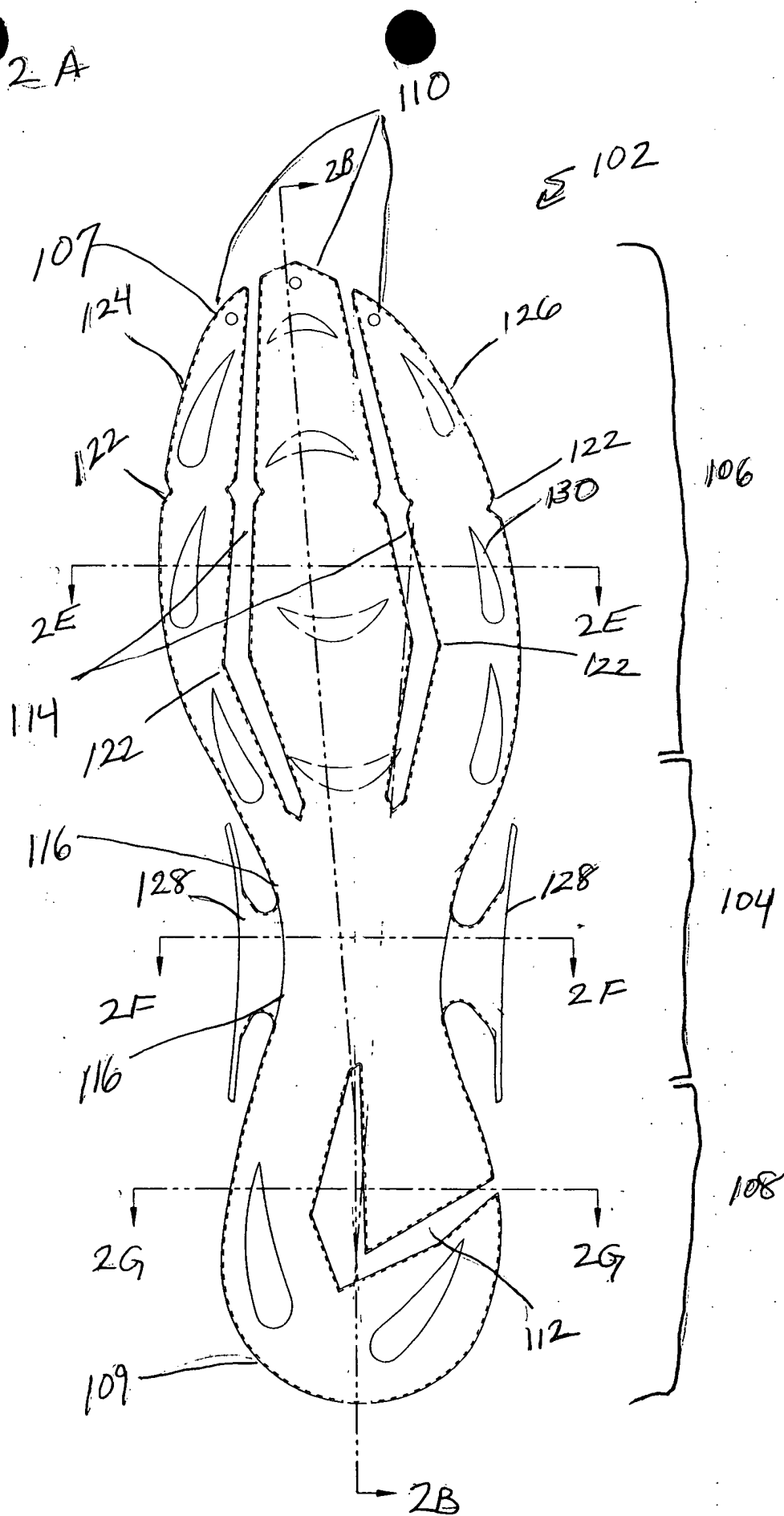


Fig 2B

SECTION 2B-2B

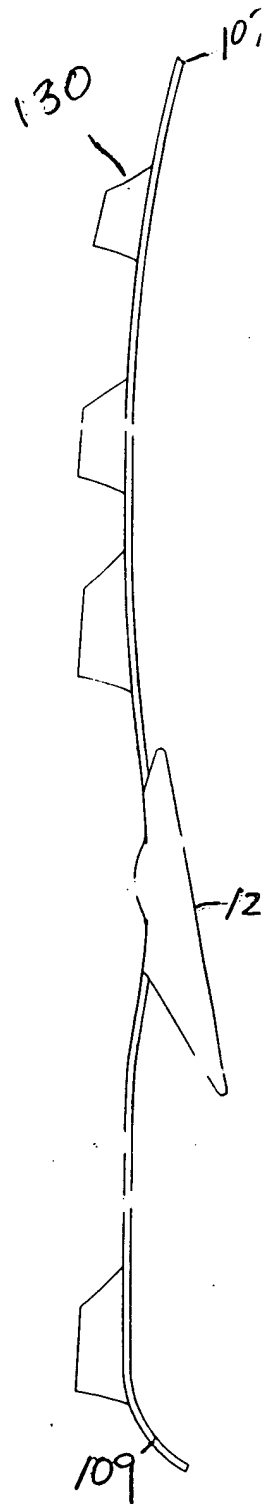
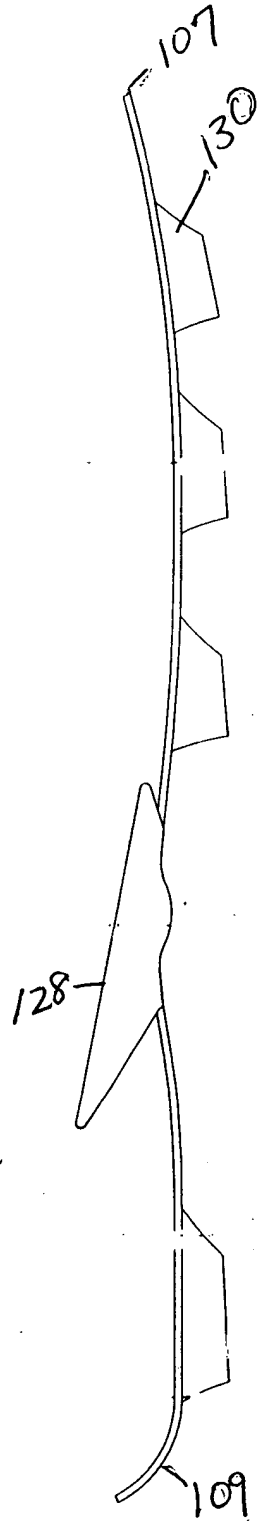


Fig 2c

Fig 2D

A cross-sectional view of a semiconductor device. It features a central channel region labeled 114, which is flanked by two side regions labeled 110. The side regions 110 are further defined by a structure labeled 130, which appears to be a gate or a contact. The device is shown in a cross-section with a central channel and side regions.

Fig 2E

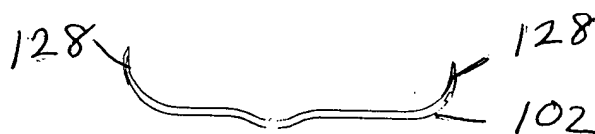


Fig 2F

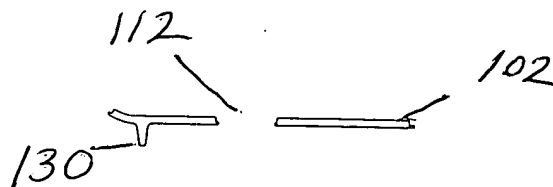


Fig 2G

Fig 3A

201

202

230

232

202

238

212

SECTION 38-38

201

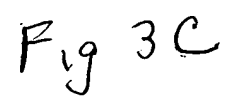


Fig 3C

238

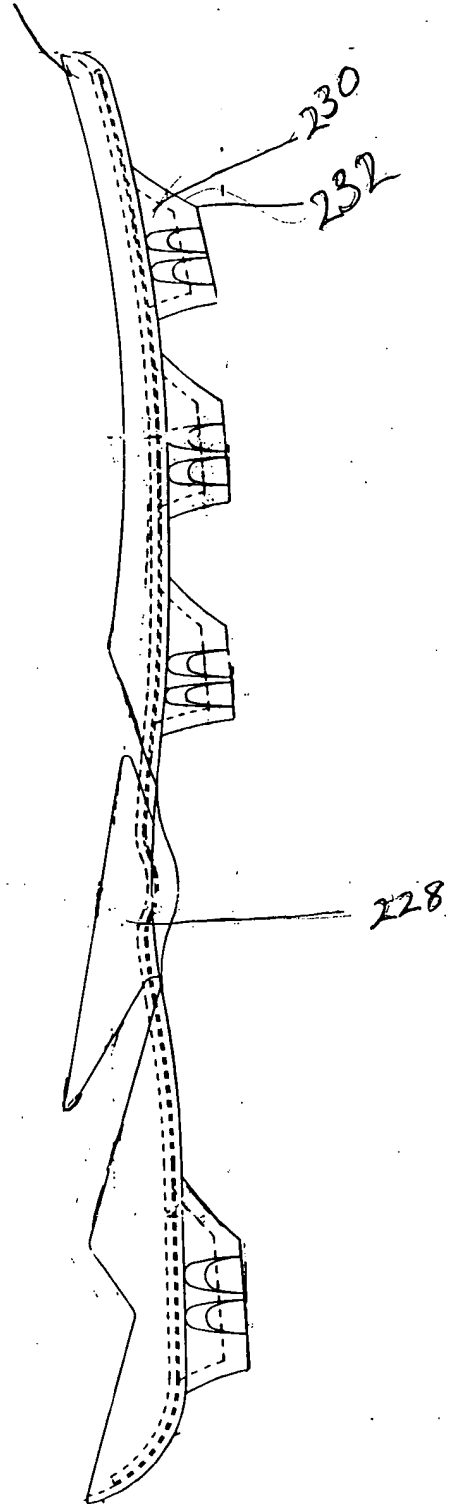


Fig 3D

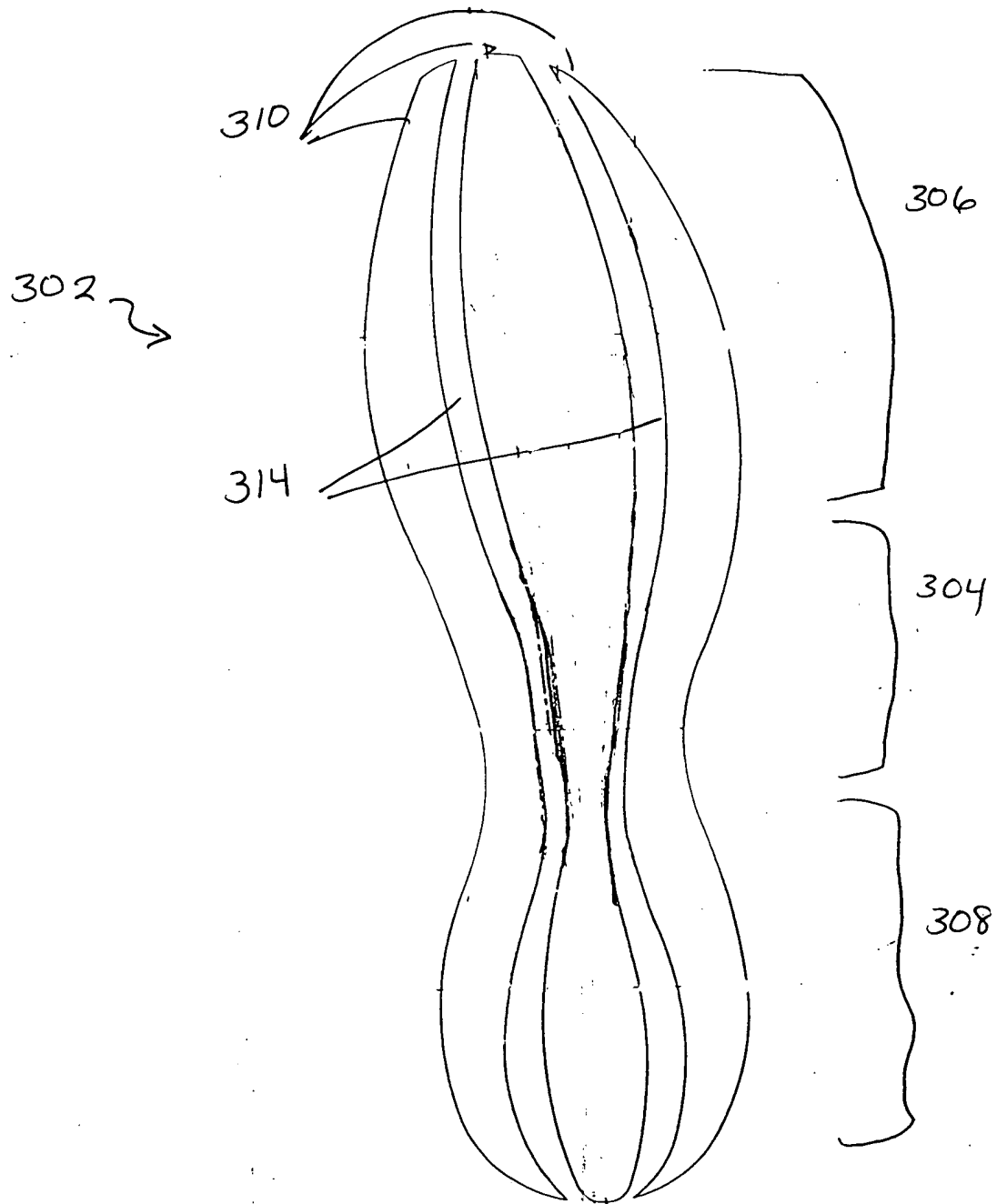
[illegible]

Fig 4.